

General Description

The operating voltage range of the SN74LVC1G34 single buffer is 1.65 V to 5.5 V .

The SN74LVC1G34 device contains one buffer and performs the Boolean function Y=A.The CMOS device has higt output drive while maintaining low static power dissipation over a broad VCC operating range.

This device is fully specified for partial-power-down applications using loff. The loff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Features

- Low Power Consumption, 10-µA Max I_{CC}
- Supports 5 V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 3.3 ns at 3.3 V

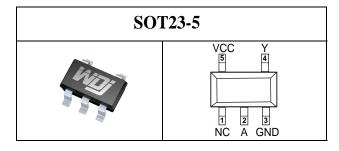
- ±24-mA Output Drive at 3.3 V
- Ioff Supports Partial-Power-Down Mode
- Typical $V_{OHV} > 2 \text{ V}$ at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$
- Typical V_{OLP} < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C

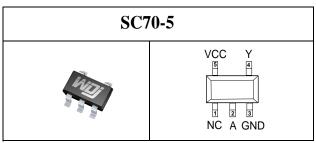
Applications

- AV Receivers
- Audio Docks: Portable
- Blu-ray Players and Home Theater
- Embedded PC
- MP3 Player/Recorder (Portable Audio)
- Personal Digital Assistant (PDA)

- Power: Telecom/Server AC/DC Supply
- Solid State Drive (SSD): Client and Enterprise
- TV: LCD/Digital and High-Definition (HDTV)
- Tablet: Enterprise
- Video Analytics: Server
- Wireless Headset, Keyboard, and Mouse

Pinning and Package

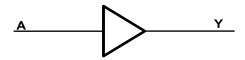




Order information

Package	Orderable Device	Packing Option
SOT23-5	SN74LVC1G34DBVRW	2000/舟
SC70-5	SN74LVC1G34DCKRW	3000/盘

Circuit Diagram





Pin Functions

Pi	n	Type	Description
Name	SOT23-5/SC70-5	туре	Description
NC	1	_	No internal connection
Α	2	I	Input
GND	3	_	Ground
Y	4	0	Output
VCC	5	_	Positive Supply

Absolute Maximum Ratings

	Parameter	Min	Max.	Unit	
Vcc	Supply volt	age range	-0.5	6.5	V
VI	Input volta	ige range	-0.5	6.5	V
Vo	Voltage range applied to any output in	the high-impedance or power-off state	-0.5	6.5	V
Vo	Voltage range applied to any output in the high or low state			Vcc+0.5	V
Iĸ	Input clamp current	V<0		-50	mA
Іок	Output clamp current	Vo<0		-50	mA
lo	Continuous o	utput current		±50	mA
	Continuous current throu	igh Vcc or GND		±100	mA
TJ	T _J Junction temperature under bias			150	°C
T _{stg}	Storage temp	erature range	-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

Symbol	Parame	Min	Max	Unit	
Vcc	Supply vo	oltage	1.65	5.5	V
Vı	Input vol	Itage	0	5.5	V
Vo	Output vo	oltage	0	Vcc	V
		V _{CC} =1.65V		-4	
		Vcc=2.3V		-8	
Іон	High-level output current	Vcc=3V		-16	mA
				-24	
		V _{CC} =4.5V		-32	
		V _{CC} =1.65V		4	
		V _{CC} =2.3V		8	
loL	Low-level output current	\/ -2\/		16	mA
		V _{CC} =3V		24	
		V _{CC} =4.5V		32	
TA	Operating free-air	r temperature	-40	125	$^{\circ}$

⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.



Electrical Characteristics

Vcc=5.0V or 3.3V, Typical values are at T_A =+25°C. (unless otherwise noted).

D	4	To al O an distance	v	-4	0°C to 85	5°C	-40	0°C to 12	5°C	Unit	
Parai	meter	Test Conditions	V _{cc}	Min	Тур	Max	Min	Тур	Max	Unit	
		Ι _{ΟΗ} =–100 μΑ	1.65 V to 5.5 V	V _{CC} -0.1			V _{CC} -0.1				
		I _{OH} =–4 mA	1.65 V	1.2			1.2				
.,		I _{OH} =–8 mA	2.3 V	1.9			1.9			,,	
V	OH	I _{OH} =–16 mA	0.1/	2.4			2.4			V	
		I _{OH} =–24 mA	3 V	2.3			2.3				
		I _{ОН} =-32 mA	4.5 V	3.8			3.8				
		I _{OL} =100 μA	1.65 V to 5.5 V			0.1			0.1		
		1G04 I _{OL} =4 mA	1.65 V			0.45			0.45		
.,	,	I _{OL} =8 mA	2.3 V			0.3			0.3	,,	
V	OL	I _{OL} =16 mA	0.14			0.4			0.4	V	
		I _{OL} =24 mA	3 V			0.55			0.55		
		I _{OL} =32 mA	4.5 V			0.55			0.55		
l _l	A input	V _i =5.5 V or GND	0 to 5.5 V			±5			±5	μA	
Ic	off	V _I or V _O =5.5 V	0			±10			±10	μA	
lo	cc	V _I =5.5 V or GND, I _O =0	1.65 V to 5.5 V			10			10	μA	
ΔΙ	lcc	One input at $V_{\text{CC}} = 0.6 \text{ V}$, Other inputs at V_{CC} or GND	3 V to 5.5 V			500			500	μА	
C	Cı	V _I =V _{CC} or GND	3.3 V		5			5		pF	

⁽¹⁾ All unused digital inputs of the device must be held at V_{cc} or GND to ensure proper device operation

Vcc=5.0V or 3.3V, Typical values are at T_A =+25°C. (unless otherwise noted).

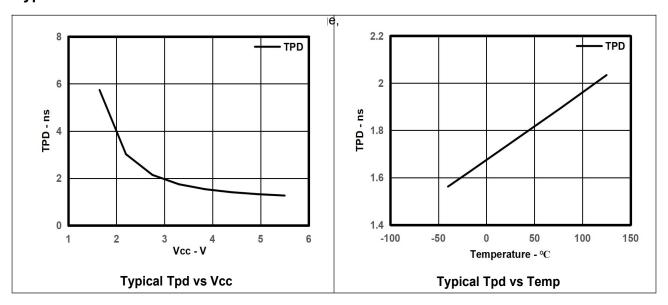
	·····		`			,						
						-40°C t	o 125°C]
Parameter	From (Input)	To (Output)		:1.8 V .15 V		:2.5 V .2 V		3.3 V .3 V	V _{cc} :	=5 V .5 V	Unit	
			Min	Max	Min	Max	Min	Max	Min	Max		
t _{pd}	Α	Y	3.9	9.5	1.4	4.5	1	3.3	1	3.0	ns	

T_A=25°C

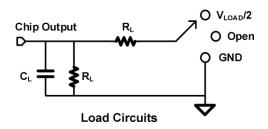
Bouwardon		T4 O	Vcc=1.8 V	V _{CC} =2.5 V	Vcc=3.3 V	Vcc=5 V	1114
	Parameter	Test Conditions	Тур	Тур	Тур	Тур	Unit
C _{pd}	Power dissipation capacitance	f=10 MHz	17	28	33	47	pF



Typical Characteristics



Parameter Measurement Information

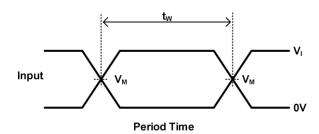


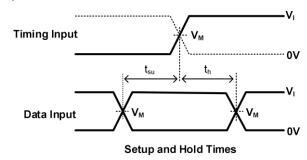
TEST	S1
T _{PHL} /T _{PLH}	OPEN
T _{PLZ} /T _{PZL}	V_{LOAD}
T _{PHZ} /T _{PZH}	GND

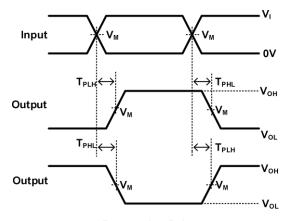
Vcc	INPUTS		V _M	V _{LOAD}	CL	R∟	VΔ
VCC	Vı	T _r /T _f	VW.	V LOAD	OL	NL	VΔ
1.8V±0.15V	Vcc	≤2ns	Vcc/2	2×V _{CC}	30pF	1kΩ	0.15V
2.5V±0.15V	Vcc	≤2ns	Vcc/2	2×Vcc	30pF	500Ω	0.15V
3.3V±0.15V	3V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V
5V±0.15V	Vcc	≤2.5ns	V _{CC} /2	2×V _{CC}	50pF	500Ω	0.3V



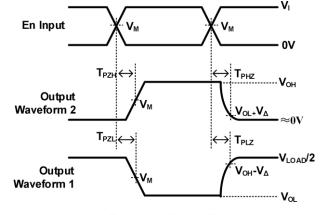
Parameter Measurement Information(Continued)







Propagation Delay for Output and Inverted Output



Enable and Disable Times Low-And High-Level Enabling

Notes:A. C_L includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control.

- D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.

Waveform 2 is for an output with internal conditions such that the F. tpz_ and tpz_H are the same as ten. output is high, except when disabled by the output control. C. All input pulses are supplied by generators having the following characteristics: PRR 10 MHz, Z =50.

- G. t_{PLH} and t_{PHL} are the same as $t_{\text{pd.}}$
- H. All parameters and waveforms are not applicable to all device.

Feature Description

The device is designed for 1.65V to 5.5V V_{CC} operation and it allows down voltage translation from 5V to 3.3V, or 3.3V to 1.8V. The input voltage of SN74LVC1G34 accepts to 5.5V.

The SN74LVC1G34 has power-down protection (off) and Schmitt-trigger input.

loff feature allows voltage on the inputs and outputs when V_{CC} is 0 V, and is able to reduce leakage when V_{CC} is 0V. Schmitt-Trigger input can improve the noise immunity capability

Device Functional Modes

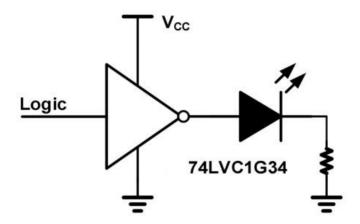
Input A	Output Y
Н	Н
L	L



Application Information

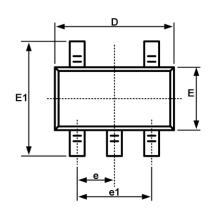
The SN74LVC1G34 is a high drive CMOS device that can be used for implementing inversion logic with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V making it Ideal for driving multiple outputs and good for high-speed applications up to 100 Mhz. The inputs are 5.5 V tolerant allowing it to translate down to V_{CC} .

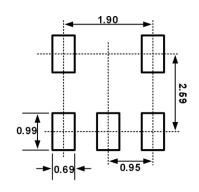
Typical Power Button Circuit



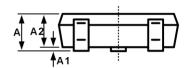


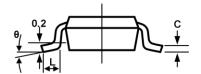
Package Outline SOT23-5





Recommended Land Pattern (Unit: mm)

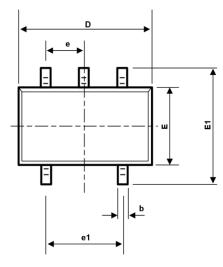


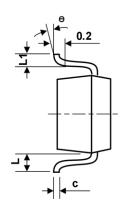


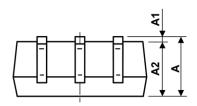
Cumbal	Dimensions	In Millimeters	Dimensions	s In Inches
Symbol	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
е	0.95	OBSC	0.037	BSC
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
L1	0.60	OREF	0.024REF	
θ	0°	8°	0°	8°



Package Outline SC70-5







aumh al	Dimension I	n Millimeters	Dimension	s In Inches
symbol	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
C	0.110	0.175	0.004	0.007
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
е	0.65	OTYP	0.026	STYP
e1	1.200	1.400	0.047	0.055
L	0.529	5REF	0.021	IREF
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°



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